

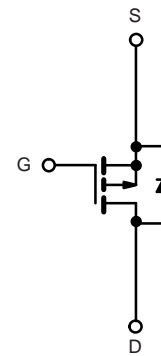
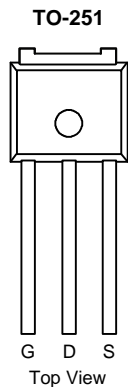
P-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY

| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) ^a |
|--------------|-----------------------------|------------------------|
| - 40 | 0.010 at $V_{GS} = - 10$ V | ± 55 |
| | 0.014 at $V_{GS} = - 4.5$ V | ± 54 |

FEATURES

- Compliant to RoHS Directive 2002/95/EC



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|----------------|----------------|-------------------|
| Gate-Source Voltage | V_{GS} | ± 40 | V |
| Continuous Drain Current ($T_J = 175$ °C) | I_D | $T_C = 25$ °C | - 55 ^a |
| | | $T_C = 125$ °C | - 52 |
| Pulsed Drain Current | I_{DM} | - 220 | A |
| Avalanche Current | I_{AR} | - 60 | |
| Repetitive Avalanche Energy ^b | E_{AR} | 180 | mJ |
| Power Dissipation | P_D | $T_C = 25$ °C | 45 |
| | | $T_A = 25$ °C | 3.75 |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 175 | °C |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Limit | Unit |
|---------------------|------------|---------------------------------|------|
| Junction-to-Ambient | R_{thJA} | PCB Mount (TO-263) ^c | 40 |
| | | Free Air (TO-220AB) | 62.5 |
| Junction-to-Case | R_{thJC} | 0.8 | °C/W |

Notes:

- Package limited.
- Duty cycle ≤ 1 %.
- When mounted on 1" square PCB (FR-4 material).
- See SOA curve for voltage derating.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

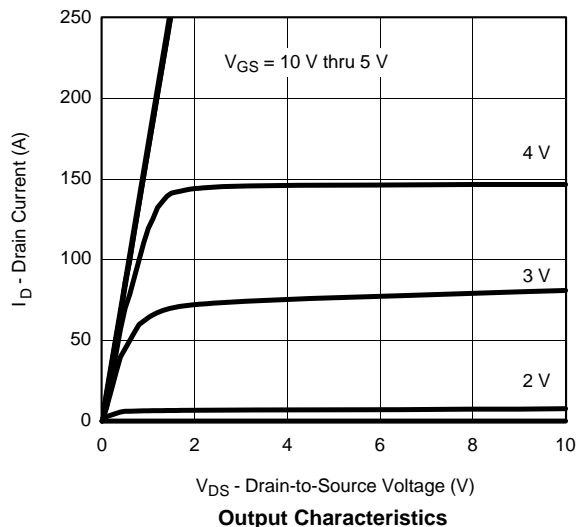
| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|--|---------------|--|-------|-------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$ | - 40 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | - 1.0 | | - 2.5 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}$ | | | - 1 | μA |
| | | $V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | | | - 50 | |
| | | $V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$ | | | - 250 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$ | - 120 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = -10\text{ V}, I_D = -30\text{ A}$ | | 0.010 | | Ω |
| | | $V_{GS} = -10\text{ V}, I_D = -30\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | | 0.016 | | |
| | | $V_{GS} = -10\text{ V}, I_D = -30\text{ A}, T_J = 175\text{ }^\circ\text{C}$ | | 0.023 | | |
| | | $V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$ | | 0.014 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = -15\text{ V}, I_D = -75\text{ A}$ | 20 | | | S |
| Dynamic^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1\text{ MHz}$ | | 3000 | | μF |
| Output Capacitance | C_{oss} | | | 620 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 315 | | |
| Total Gate Charge ^c | Q_g | $V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -75\text{ A}$ | | 160 | | nC |
| Gate-Source Charge ^c | Q_{gs} | | | 32 | | |
| Gate-Drain Charge ^c | Q_{gd} | | | 30 | | |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = -15\text{ V}, R_L = 0.2\text{ }\Omega$ $I_D \equiv -75\text{ A}, V_{GEN} = -10\text{ V}, R_g = 2.5\text{ }\Omega$ | | 25 | 40 | ns |
| Rise Time ^c | t_r | | | 225 | 360 | |
| Turn-Off Delay Time ^c | $t_{d(off)}$ | | | 150 | 240 | |
| Fall Time ^c | t_f | | | 210 | 340 | |
| Source-Drain Diode Ratings and Characteristics^b ($T_C = 25\text{ }^\circ\text{C}$) | | | | | | |
| Continuous Current | I_S | | | - 220 | | A |
| Pulsed Current | I_{SM} | | | | - 240 | |
| Forward Voltage ^a | V_{SD} | $I_F = -75\text{ A}, V_{GS} = 0\text{ V}$ | | - 1.2 | - 1.5 | V |
| Reverse Recovery Time | t_{rr} | $I_F = -75\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 55 | 100 | ns |
| Peak Reverse Recovery Current | $I_{RM(REC)}$ | | | 2.5 | 5 | A |
| Reverse Recovery Charge | Q_{rr} | | | 0.07 | 0.25 | μC |

Notes:

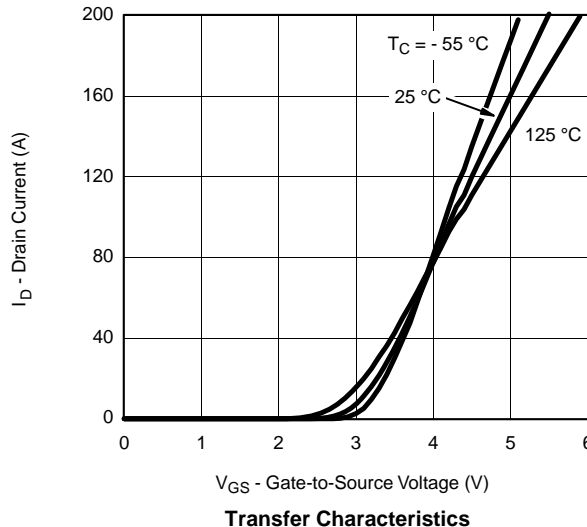
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

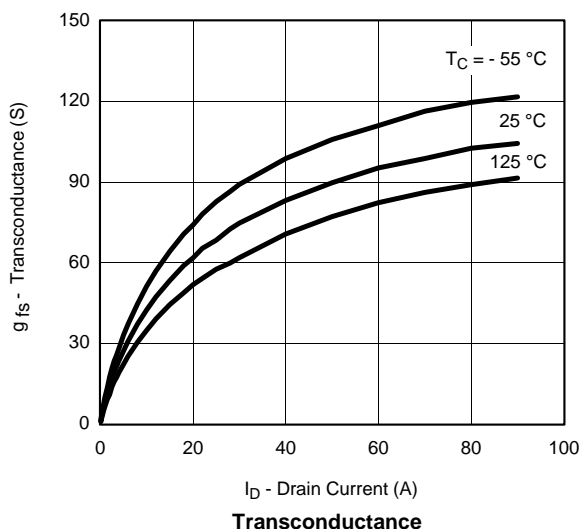
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



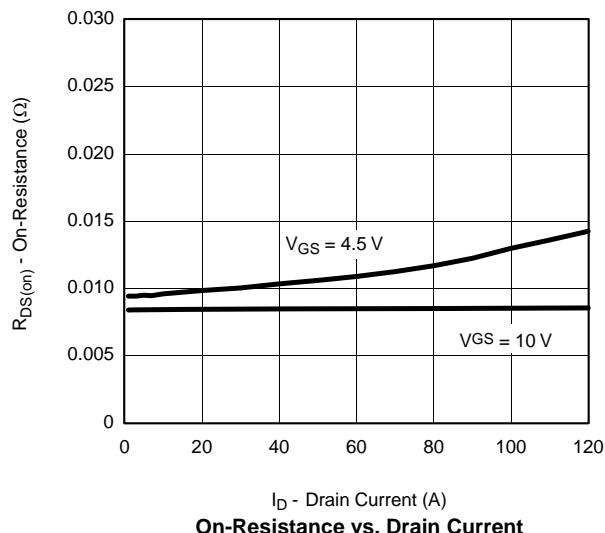
Output Characteristics



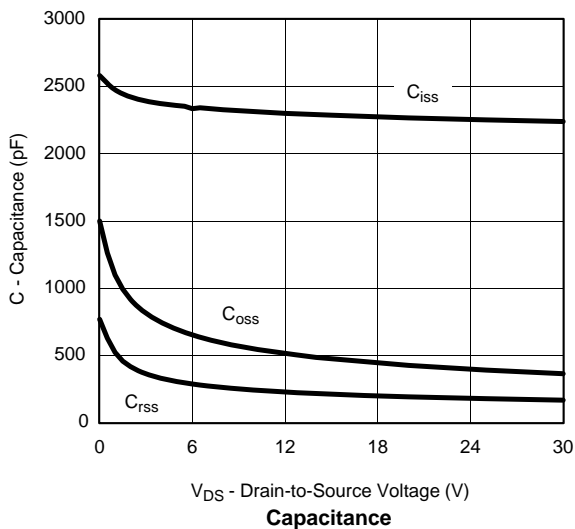
Transfer Characteristics



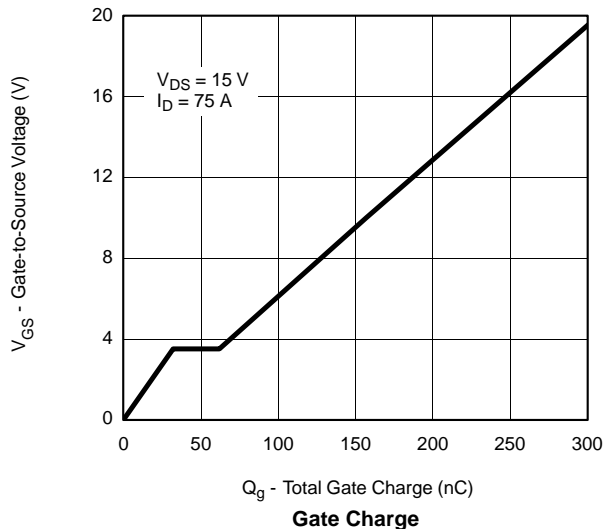
Transconductance



On-Resistance vs. Drain Current

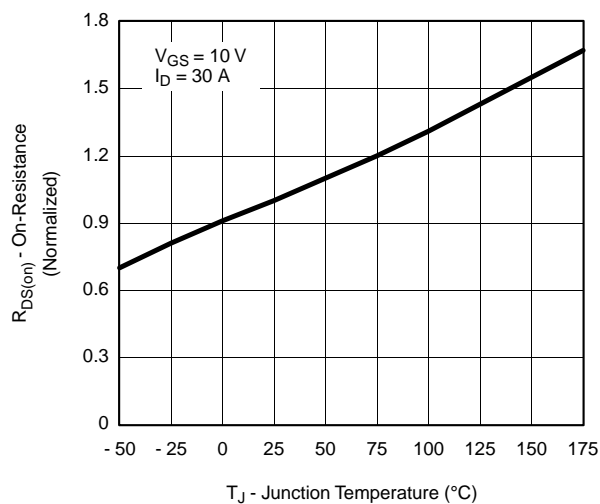


Capacitance

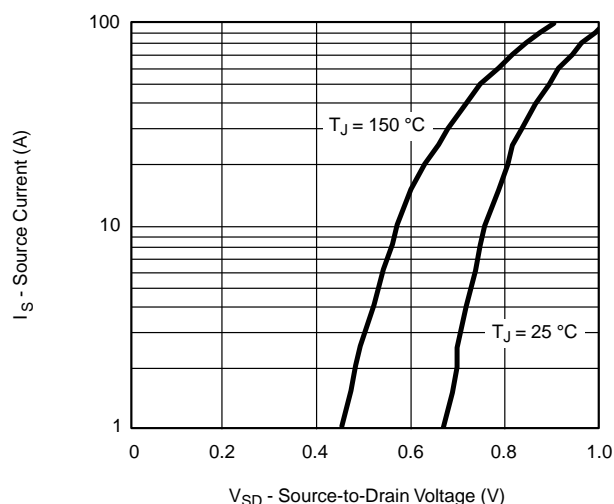


Gate Charge

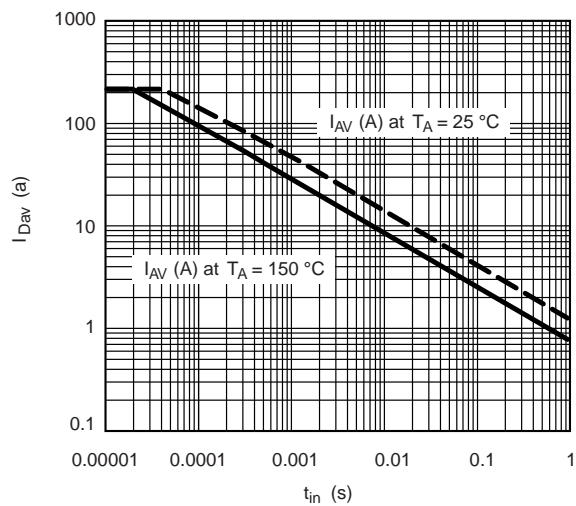
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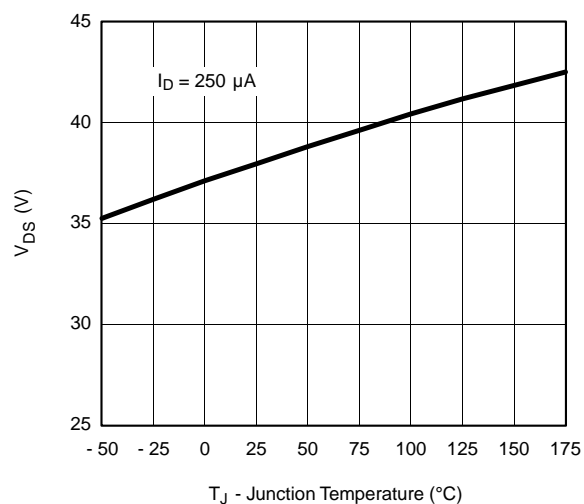
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

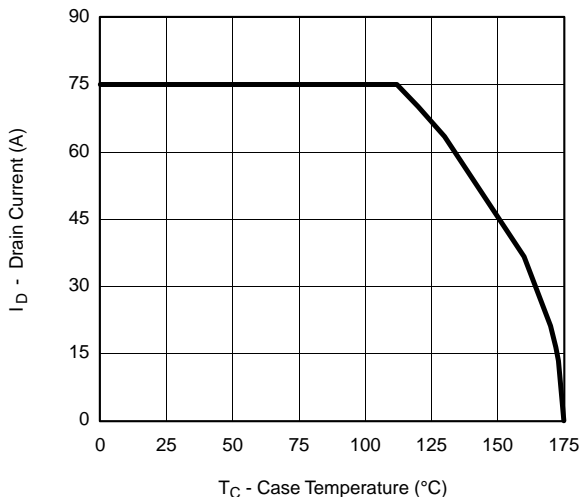


Avalanche Current vs. Time

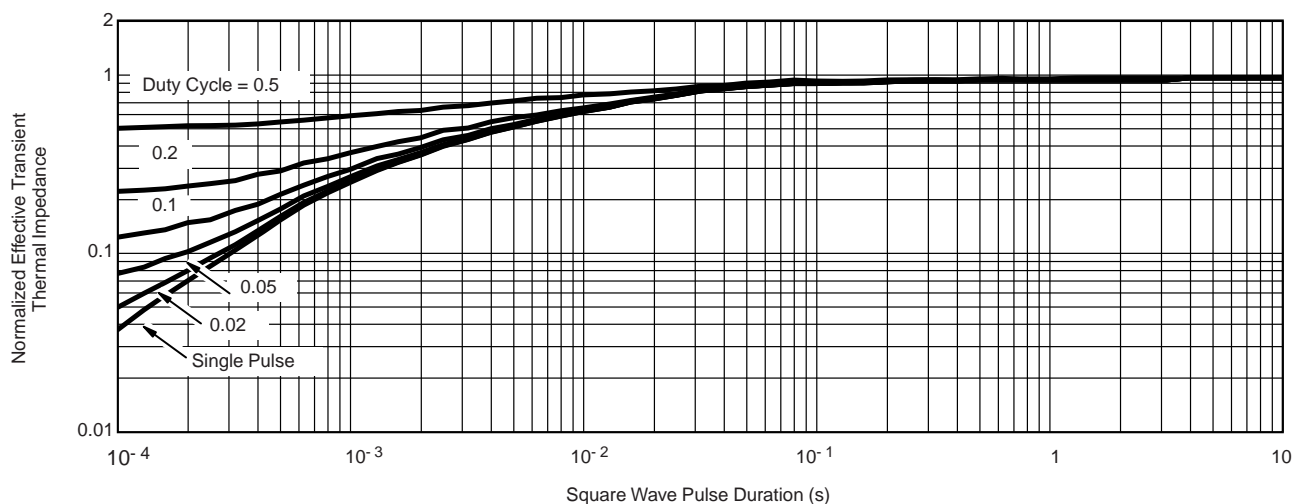
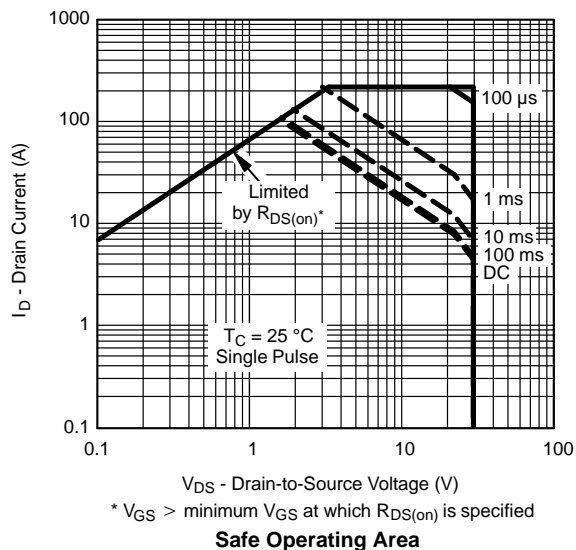


Drain Source Breakdown vs. Junction Temperature

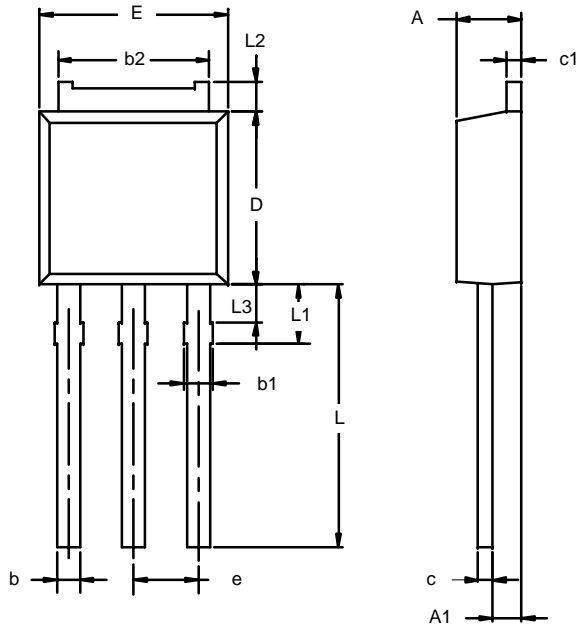
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature



TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

| Dim | MILLIMETERS | | INCHES | |
|---|-------------|------|-----------|-------|
| | Min | Max | Min | Max |
| A | 2.21 | 2.38 | 0.087 | 0.094 |
| A1 | 0.89 | 1.14 | 0.035 | 0.045 |
| b | 0.71 | 0.89 | 0.028 | 0.035 |
| b1 | 0.76 | 1.14 | 0.030 | 0.045 |
| b2 | 5.23 | 5.43 | 0.206 | 0.214 |
| c | 0.46 | 0.58 | 0.018 | 0.023 |
| c1 | 0.46 | 0.58 | 0.018 | 0.023 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| E | 6.48 | 6.73 | 0.255 | 0.265 |
| e | 2.28 BSC | | 0.090 BSC | |
| L | 8.89 | 9.53 | 0.350 | 0.375 |
| L1 | 1.91 | 2.28 | 0.075 | 0.090 |
| L2 | 0.89 | 1.27 | 0.035 | 0.050 |
| L3 | 1.15 | 1.52 | 0.045 | 0.060 |
| ECN: S-03946—Rev. E, 09-Jul-01 DWG: 5346 | | | | |

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